

Amendments to the Specification:

Please replace the paragraph beginning on page 5, line 21, with the following rewritten paragraph:

Reference is now made to FIG. 2 to FIG. 9 to give a detailed description of the patterned thin film and the method of forming the same of the embodiment. In the embodiment a frame having an undercut near the bottom thereof is utilized to form the patterned thin film by frame plating. A 'two-layer resist' is utilized to form the above-mentioned frame in the embodiment. The two-layer resist is a two-layer film having a first layer that is a lower layer and a second ~~later~~ layer that is an upper layer, wherein at least the second layer is made of a resist. The two-layer resist is disclosed in, for example, the U. S. Patent No. 5,721,078, the U. S. Patent No. 5,725,997, and the U. S. Patent No. 5,747,198.

Please replace the paragraph beginning on page 6, line 5, with the following rewritten paragraph:

According to the method of forming the patterned thin film of the embodiment, as shown in FIG. 2, an electrode film 2 is formed by sputtering, for example, on a substrate 1. The substrate 1 may be made of a semiconductor such as silicon (Si), or a ceramic such as aluminum oxide and titanium carbide (Al₂O₃-TiC), or a resin such as polyethylene terephthalate. The electrode film 2 is made of a conductive material such as a metal. The electrode film 2 is preferably made of a material having a composition the same as that of a material of which the patterned thin film to be formed on the electrode film 2 ~~are~~ is made. The electrode film 2 may be made up of a single layer or a plurality of layers, and made of copper (Cu), for example.